

Walter Meyer

List of Publications by Year in descending order

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489802

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#	ARTICLE	IF	CITATIONS
1	DLTS study of the influence of annealing on deep level defects induced in xenon ions implanted n-type 4H-SiC. <i>Journal of Materials Science: Materials in Electronics</i> , 2022, 33, 15679-15688.	1.1	2
2	Effect of Isovalent Doping on Hydrogen Passivated Vacancy-oxygen Defect Complexes in Silicon: Insights from Density Functional Theory. <i>Silicon</i> , 2021, 13, 1969-1977.	1.8	2
3	Deep-level transient spectroscopy of GaN grown by electrochemical deposition and irradiated with alpha particles. <i>Materials Science in Semiconductor Processing</i> , 2021, 127, 105685.	1.9	3
4	First-principles Study of the Impact of Hydrogen Passivation on the Charge State Transition Levels of the $\text{CiO}_i(\text{Sii})_n$ Defect Complexes in Silicon. <i>Silicon</i> , 2020, 12, 2699-2704.	1.8	1
5	Effect of electron radiation on small-signal parameters of NMOS devices at mm-wave frequencies. <i>Microelectronics Reliability</i> , 2020, 107, 113598.	0.9	2
6	Ti- and Fe-related charge transition levels in $\text{In}^{2+}\text{Ga}_2\text{O}_3$. <i>Applied Physics Letters</i> , 2020, 116, .	1.5	37
7	Determination of capture barrier energy of the E-center in palladium Schottky barrier diodes of antimony-doped germanium by varying the pulse width. <i>Materials Research Express</i> , 2020, , .	0.8	2
8	Ab initio study of the effect of hydrogen passivation on boron-oxygen-carbon related defect complexes in silicon. <i>Materials Science in Semiconductor Processing</i> , 2020, 110, 104967.	1.9	3
9	Electrical characterization of electron beam exposure induced defects in epitaxially grown n-type silicon. <i>AIP Conference Proceedings</i> , 2019, , .	0.3	1
10	Effects of thermal treatment on structural, optical and electrical properties of NiO thin films. <i>Physica B: Condensed Matter</i> , 2019, 575, 411694.	1.3	15
11	Influence (Ce and Sm) co-doping ZnO nanorods on the structural, optical and electrical properties of the fabricated Schottky diode using chemical bath deposition. <i>Journal of Alloys and Compounds</i> , 2019, 810, 151929.	2.8	18
12	Electronic properties and defect levels induced by group III substitutional interstitial complexes in Ge. <i>Journal of Materials Science</i> , 2019, 54, 10798-10808.	1.7	4
13	The influence of thermal annealing on the characteristics of Au/Ni Schottky contacts on n-type 4H-SiC. <i>Applied Physics A: Materials Science and Processing</i> , 2018, 124, 1.	1.1	6
14	Electrically active induced energy levels and metastability of B and N vacancy-complexes in 4H-SiC. <i>Journal of Physics Condensed Matter</i> , 2018, 30, 185702.	0.7	4
15	Structural, optical and electrical characteristics of nickel oxide thin films synthesised through chemical processing method. <i>Physica B: Condensed Matter</i> , 2018, 535, 24-28.	1.3	15
16	Electrically active defects in p-type silicon after alpha-particle irradiation. <i>Physica B: Condensed Matter</i> , 2018, 535, 99-101.	1.3	3
17	Laplace DLTS study of the fine structure and metastability of the radiation-induced E3 defect level in GaAs. <i>Semiconductor Science and Technology</i> , 2018, 33, 125011.	1.0	2
18	7. Metastability of the boron-vacancy complex in silicon: Insights from hybrid functional calculations. , 2018, , 113-122.		0

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19	Metastability of the boron-vacancy complex in silicon: Insights from hybrid functional calculations. <i>Physical Sciences Reviews</i> , 2018, 3, .	0.8	0
20	Properties of a previously unobserved donor-related electrically active defect in Ge induced by alpha particle irradiation. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2017, 406, 680-682.	0.6	1
21	Ab-initio Study of Aluminium Impurity and Interstitial-Substitutional Complexes in Ge Using a Hybrid Functional (HSE). <i>Journal of Electronic Materials</i> , 2017, 46, 3880-3887.	1.0	7
22	Rare Earth Interstitials in Ge: A Hybrid Density Functional Theory Study. <i>Journal of Electronic Materials</i> , 2017, 46, 1022-1029.	1.0	8
23	Electrical Characterization of High Energy Electron Irradiated Ni/4H-SiC Schottky Barrier Diodes. <i>Journal of Electronic Materials</i> , 2016, 45, 4177-4182.	1.0	13
24	The carbon-substitutional-carbon-interstitial (CsCi) defect pair in silicon from hybrid functional calculations. <i>Computational Materials Science</i> , 2016, 118, 338-341.	1.4	6
25	Electrical characterization of deep levels created by bombarding nitrogen-doped 4H-SiC with alpha-particle irradiation. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2016, 371, 312-316.	0.6	23
26	Electrical Characterization of Defects Introduced in <i>n</i> -Type N-Doped 4H-SiC during Electron Beam Exposure. <i>Solid State Phenomena</i> , 2015, 242, 427-433.	0.3	3
27	Determination of the mean and the homogeneous barrier height of Cu Schottky contacts on heteroepitaxial $\text{InGa}_{2/3}\text{O}_3$ thin films grown by pulsed laser deposition. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2014, 211, 40-47.	0.8	111
28	Observation of low-temperature annealing of a primary defect in gallium nitride. <i>Physica B: Condensed Matter</i> , 2014, 439, 64-66.	1.3	1
29	Ab initio study of metastability of Eu^{3+} defect complexes in GaN. <i>Physica B: Condensed Matter</i> , 2014, 439, 141-143.	1.3	6
30	Introduction and annealing of primary defects in proton-bombarded n-GaN . <i>Physica Status Solidi (B): Basic Research</i> , 2014, 251, 211-218.	0.7	5
31	A study of the T2 defect and the emission properties of the E3 deep level in annealed melt grown ZnO single crystals. <i>Journal of Applied Physics</i> , 2013, 113, 124502.	1.1	9
32	Field dependence of the E1 ² and M3 ² electron traps in inductively coupled Ar plasma treated n-Gallium Arsenide. <i>Journal of Applied Physics</i> , 2012, 111, 093703.	1.1	1
33	Effects of high temperature annealing on single crystal ZnO and ZnO devices. <i>Journal of Applied Physics</i> , 2012, 111, .	1.1	15
34	Effects of hydrogen, oxygen, and argon annealing on the electrical properties of ZnO and ZnO devices studied by current-voltage, deep level transient spectroscopy, and Laplace DLTS. <i>Journal of Applied Physics</i> , 2012, 111, 094504.	1.1	29
35	Electrical characterization of defects introduced in n-Si during electron beam deposition of Pt. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2012, 209, 1926-1933.	0.8	9
36	Ar plasma induced deep levels in epitaxial n-GaAs. <i>Journal of Applied Physics</i> , 2012, 111, 013703.	1.1	5

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37	Inductively coupled plasma induced deep levels in epitaxial n-GaAs. <i>Physica B: Condensed Matter</i> , 2012, 407, 1497-1500.	1.3	5
38	Characterization of AlGaIn-based metal-semiconductor solar-blind UV photodiodes with IrO ₂ Schottky contacts. <i>Physica B: Condensed Matter</i> , 2012, 407, 1529-1532.	1.3	6
39	Interface properties of an O ₂ annealed Au/Ni/n-Al _{0.18} Ga _{0.82} N Schottky contact. <i>Physica B: Condensed Matter</i> , 2012, 407, 1599-1602.	1.3	0
40	Optoelectronic characterization of Au/Ni/n-AlGaIn photodiodes after annealing at different temperatures. <i>Physica B: Condensed Matter</i> , 2012, 407, 1628-1630.	1.3	4
41	Comparison of two models for phonon assisted tunneling field enhanced emission from defects in Ge measured by DLTS. <i>Physica B: Condensed Matter</i> , 2012, 407, 1641-1644.	1.3	1
42	A comparative study of the electrical properties of Pd/ZnO Schottky contacts fabricated using electron beam deposition and resistive/thermal evaporation techniques. <i>Journal of Applied Physics</i> , 2011, 110, 094504.	1.1	13
43	Defect introduction in Ge during inductively coupled plasma etching and Schottky barrier diode fabrication processes. <i>Thin Solid Films</i> , 2010, 518, 2485-2488.	0.8	8
44	The dependence of barrier height on temperature for Pd Schottky contacts on ZnO. <i>Physica B: Condensed Matter</i> , 2009, 404, 4402-4405.	1.3	34
45	Current-temperature measurements of a SBD evaporated onto inductively coupled plasma cleaned germanium. <i>Physica B: Condensed Matter</i> , 2009, 404, 4389-4392.	1.3	0
46	Electronic and annealing properties of the E0.31 defect introduced during Ar plasma etching of germanium. <i>Physica B: Condensed Matter</i> , 2009, 404, 4376-4378.	1.3	8
47	Electrical characterization of defects introduced in Ge during electron beam deposition of different metals. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2008, 205, 159-161.	0.8	11
48	Electrical characterization of defects introduced during metallization processes in n-type germanium. <i>Materials Science in Semiconductor Processing</i> , 2008, 11, 348-353.	1.9	4
49	Electronic properties of shallow level defects in ZnO grown by pulsed laser deposition. <i>Journal of Physics: Conference Series</i> , 2008, 100, 042038.	0.3	4
50	Dependence of Trap Concentrations in ZnO Thin Films on Annealing Conditions. <i>Journal of the Korean Physical Society</i> , 2008, 53, 2861-2863.	0.3	17
51	Electrical characterization of defects in heavy-ion implanted n-type Ge. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2007, 257, 169-171.	0.6	9
52	Electronic properties of defects in pulsed-laser deposition grown ZnO with levels at 300 and 370meV below the conduction band. <i>Physica B: Condensed Matter</i> , 2007, 401-402, 378-381.	1.3	30
53	Electrical Characterization of Defects Introduced During Sputter Deposition of Schottky Contacts on n-type Ge. <i>Journal of Electronic Materials</i> , 2007, 36, 1604-1607.	1.0	9
54	Electrical characterization of defects introduced during electron beam deposition of Schottky contacts on n-type Ge. <i>Materials Science in Semiconductor Processing</i> , 2006, 9, 576-579.	1.9	10

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55	Electrical Characterization of Proton Irradiated n-Type ZnO. Materials Research Society Symposia Proceedings, 2006, 957, 1.	0.1	0
56	Electrical characterization of defects introduced during electron beam deposition of Pd Schottky contacts on n-type Ge. Applied Physics Letters, 2006, 88, 242110.	1.5	38
57	Electrical characterization of defects introduced in n-type Ge during indium implantation. Applied Physics Letters, 2006, 89, 152123.	1.5	15
58	Reactivation and passivation of the $E_c - 0.61$ eV deep level in GaN. Physica Status Solidi A, 2004, 201, 2277-2280.	1.7	2
59	Electrical characterisation of hole traps in n-type GaN. Physica Status Solidi A, 2004, 201, 2271-2276.	1.7	29
60	Electrical characterisation of NiO/ZnO structures. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 674-677.	0.8	15
61	Effect of thermal radiation on electron emission from the E2 defect in n-GaAs. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 2333-2336.	0.8	0
62	Fabrication and characterisation of NiO/ZnO structures. Sensors and Actuators B: Chemical, 2004, 100, 270-276.	4.0	57
63	Electrical characterization of as-grown and particle irradiated n-type bulk ZnO. , 2004, , .		0
64	Bias-dependent deep level in HVPE n-GaN. Physica B: Condensed Matter, 2003, 340-342, 475-478.	1.3	9
65	Electrical defects introduced during high-temperature irradiation of GaN and AlGaIn. Physica B: Condensed Matter, 2003, 340-342, 421-425.	1.3	23
66	Electron emission properties of a defect at $\frac{1}{4}(E_c + 0.23\text{eV})$ in impurity-free disordered n-GaAs. Physica B: Condensed Matter, 2003, 340-342, 315-319.	1.3	1
67	Defect Engineering and Atomic Relocation Processes in Impurity-Free Disordered GaAs and AlGaAs. Materials Research Society Symposia Proceedings, 2003, 799, 1.	0.1	0
68	Electrical characterization of vapor-phase-grown single-crystal ZnO. Applied Physics Letters, 2002, 80, 1340-1342.	1.5	171
69	Electron traps created in n-type GaN during 25 keV hydrogen implantation. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 93, 6-9.	1.7	3
70	Defects Created by 25 keV Hydrogen Implantation in n-type GaN. Materials Research Society Symposia Proceedings, 2001, 693, 44.	0.1	0
71	Electrical characterization of growth-induced defects in n-GaN. Radiation Effects and Defects in Solids, 2001, 156, 255-259.	0.4	4
72	Metallisation induced electron traps in epitaxially grown n-type GaN. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2000, 71, 77-81.	1.7	10

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73	Configurational metastable defects in irradiated epitaxially grown boron-doped p-type Si. Physical Review B, 2000, 63, .	1.1	13
74	Metastable-like behaviour of a sputter deposition-induced electron trap in n-GaN. Physica B: Condensed Matter, 1999, 273-274, 92-95.	1.3	18
75	Emission kinetics of electron traps introduced in n-GaN during He-ion irradiation. Nuclear Instruments & Methods in Physics Research B, 1999, 148, 474-477.	0.6	7
76	The influence of high-energy alpha-particle irradiation on the spectral and defect properties of a Si photovoltaic detector. Semiconductor Science and Technology, 1999, 14, 323-326.	1.0	7
77	Electric-field-enhanced emission and annealing behaviour of electron traps introduced in n-Si by low-energy He ion bombardment. Semiconductor Science and Technology, 1999, 14, 41-47.	1.0	35
78	Summary of Schottky barrier height data on epitaxially grown n- and p-GaAs. Thin Solid Films, 1998, 325, 181-186.	0.8	40
79	Electronic and transformation properties of a metastable defect introduced in epitaxially grown boron-doped p-type Si by alpha particle irradiation. Applied Physics Letters, 1998, 72, 3178-3180.	1.5	9
80	A deep level transient spectroscopy characterization of defects induced in epitaxially grown n-Si by low-energy He-ion bombardment. Journal of Applied Physics, 1998, 83, 5576-5578.	1.1	16
81	Electrical characterization of He-plasma processed n-GaAs. Journal of Applied Physics, 1998, 84, 1973-1976.	1.1	7
82	Fermi level pinning by metal Schottky contacts on n type GaAs. Materials Science and Technology, 1998, 14, 1269-1272.	0.8	3
83	Characterization of a Metastable Defect Introduced In Epitaxially Grown Boron Doped Si by 5.4 MeV α -Particles. Materials Research Society Symposia Proceedings, 1998, 510, 449.	0.1	0
84	Electrical characterization of defects in SiCl ₄ plasma-etched n-GaAs and Pd Schottky diodes fabricated on it. Applied Physics Letters, 1997, 71, 668-670.	1.5	1
85	Electrical and Optical Characterisation of Defects Induced in Epitaxially Grown n-Si During 1 keV Noble Gas Ion Bombardment. Materials Science Forum, 1997, 258-263, 565-570.	0.3	0
86	Electrical Characterization of Defects Introduced During Plasma-Based Processing of GaAs. Materials Science Forum, 1997, 258-263, 1045-1050.	0.3	0
87	Defect Formation by Low Energy Ions during Sputter Deposition of TiW and Au on Epitaxially Grown n-Si at Different Plasma Pressures. Materials Science Forum, 1997, 248-249, 249-252.	0.3	0
88	Electronic properties of defects created in epitaxially grown n-Si by low energy He and Ar ions. Nuclear Instruments & Methods in Physics Research B, 1997, 127-128, 393-396.	0.6	0
89	Electrical Characterization Of Defects Introduced During Plasma-Based Processing Of GaAs. Materials Research Society Symposia Proceedings, 1996, 442, 51.	0.1	1
90	Optical And Electrical Characterisation Study Of SiCl ₄ Reactive Ion Etched GaAs. Materials Research Society Symposia Proceedings, 1996, 442, 75.	0.1	1

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91	Electronic Properties Of Defects Formed In n-Si During Sputter-Etching In An Ar Plasma. Materials Research Society Symposia Proceedings, 1996, 442, 87.	0.1	0
92	Metal contacts to gallium arsenide. Journal of Electronic Materials, 1996, 25, 1695-1702.	1.0	17
93	Electric Field Enhanced Emission from Two Alpha-Particle Irradiation Induced Traps in n-GaAs. Japanese Journal of Applied Physics, 1996, 35, L1-L3.	0.8	8
94	Electronic and annealing properties of a metastable He-ion implantation induced defect in GaAs. Nuclear Instruments & Methods in Physics Research B, 1995, 106, 323-327.	0.6	17
95	New electron irradiation induced electron trap in epitaxially grown Si-doped n-GaAs. Applied Physics Letters, 1995, 67, 3277-3279.	1.5	8
96	Electronic and transformation properties of a metastable defect introduced in n-type GaAs by α -particle irradiation. Physical Review B, 1995, 51, 17521-17525.	1.1	17
97	Electric-field-enhanced emission from radiation-induced hole traps in p-GaAs. Semiconductor Science and Technology, 1995, 10, 1376-1381.	1.0	16
98	Electric Field Effect on the Emission of Electron-Irradiation-Induced Defects in n-GaAs. Japanese Journal of Applied Physics, 1994, 33, 1949-1953.	0.8	9
99	Hole defects in molecular beam epitaxially grown n-GaAs introduced by alpha irradiation. Journal of Applied Physics, 1994, 75, 1222-1224.	1.1	6
100	Fermi level pinning by various metal Schottky contacts on (100) OMVPE-grown n-GaAs. Thin Solid Films, 1994, 249, 95-99.	0.8	4
101	The effect of alpha-particle and proton irradiation on the electrical and defect properties of n-GaAs. Nuclear Instruments & Methods in Physics Research B, 1994, 90, 349-353.	0.6	44
102	Electrical characteristics of neutron irradiation induced defects in n-GaAs. Nuclear Instruments & Methods in Physics Research B, 1994, 90, 387-391.	0.6	18
103	Ruthenium and ruthenium-based contacts to GaAs. Applied Surface Science, 1993, 70-71, 511-514.	3.1	8
104	Electrical characterization of defects introduced in n-GaAs by alpha and beta irradiation from radionuclides. Applied Physics A: Solids and Surfaces, 1993, 56, 547-553.	1.4	45
105	Electrical and defect characterization of n-Type GaAs irradiated with α -particles using a van de graaff accelerator and an Am-241 radio-nuclide source. Physica Status Solidi A, 1993, 140, 381-390.	1.7	8
106	Effect of electron-beam deposition rate on the electrical properties of Ti/ and Pt/n-GaAs contacts. Thin Solid Films, 1993, 235, 163-168.	0.8	1
107	Deep Level Transient Spectroscopy Characterization of Electron Irradiation Induced Hole Traps in p-GaAs Grown by Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 1993, 32, L974-L977.	0.8	14
108	Electrical characteristics of Ar-ion sputter induced defects in epitaxially grown n-GaAs. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1992, 10, 2366.	1.6	32

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109	Modified sample holder for low-temperature deep-level transient spectroscopy, current-voltage and capacitance-voltage measurements. Review of Scientific Instruments, 1992, 63, 2101-2102.	0.6	3
110	Vacuum annealing characteristics of electron beam evaporated ruthenium contacts to n-GaAs grown by organometallic vapour phase epitaxy. Thin Solid Films, 1992, 213, 113-116.	0.8	7
111	Electrical Characterization of Metastable Defects Introduced in GaN by Eu-Ion Implantation. Materials Science Forum, 0, 679-680, 804-807.	0.3	5